

IN THE CLAIMS

Please amend the claims as follows. This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (currently amended) An ~~apparatus~~ product suitable for simulating a standard wafer in semiconductor manufacturing equipment, comprising:

a ~~support~~ first layer composed of a material suitable for being handled by the semiconductor manufacturing equipment; and

a second layer composed of a mixture of multiple materials disposed entirely over the first layer ~~mixture including a process agent and a material~~, the mixture of the multiple materials configured to simultaneously generate byproducts during an etching operation ~~being applied to the support layer~~, wherein the byproducts are similar to byproducts produced by the standard wafer apparatus ~~simulates a wafer including the material and having the process agent thereon~~.

2. (currently amended) The ~~apparatus~~ product of claim 1, wherein the multiple materials include a photoresist and a metal ~~process agent is photoresist~~.

3. (currently amended) The ~~apparatus~~ product of claim 1, wherein the multiple materials include both a polymer and a material selected from the group consisting of is silicon and the apparatus simulates a wafer including polysilicon ~~silicon, tungsten, tungsten silicide, titanium, titanium nitride, silicon dioxide, aluminum, platinum, ruthenium, ruthenium oxide, copper, tantalum, and nickel~~.

Claims 4-15 (canceled)

16. (currently amended) The ~~apparatus~~ product of claim 1, wherein the mixture of multiple materials includes three or more materials ~~support layer is at least one of a disc and a wafer.~~

17. (currently amended) The ~~apparatus~~ product of claim 1, wherein the second layer is capable of withstanding cumulative etching time of up to 120 radio frequency minutes ~~support layer includes at least one of silicon, metal, plastic, and an oxide.~~

18. (currently amended) The ~~apparatus~~ product of claim 1, wherein the mixture of the multiple materials ~~and the process agent of the mixture~~ are baked on the support first layer.

19. (currently amended) The apparatus of claim 1, wherein a ratio of the multiple materials in the mixture ~~between the material to the process agent~~ corresponds to an exposed area on the standard wafer ~~to be~~ being simulated.